

IN THE CLAIMS:

Please cancel claims 1-3, and amend the claims as follows:

1-3. (Canceled)

4. (Original) A method of processing a substrate having a low k dielectric material layer formed thereover, comprising:

depositing a titanium nitride layer over the low k dielectric material layer by providing a titanium-containing compound and a nitrogen-containing compound;

soaking the titanium nitride layer in a silicon-containing gas ambient to form a titanium silicon nitride layer; and

depositing a copper seed layer over the titanium silicon nitride layer by self-ionizing plasma physical vapor deposition.

5. (Currently Amended) The method of claim 4, wherein the titanium-containing compound is selected from the group ~~including~~ consisting of tetrakisdimethylamino titanium (TDMAT) and tetrakisdiethylamino titanium (TDEAT).

6. (Original) The method of claim 5, wherein the silicon-containing gas ambient comprises silane.

7. (Currently Amended) A method of processing a substrate having a low k dielectric material layer formed thereover, comprising:

depositing a titanium nitride layer over the low k dielectric material layer by providing a titanium-containing compound selected from the group ~~including~~ consisting of tetrakisdimethylamino titanium (TDMAT) and tetrakisdiethylamino titanium (TDEAT) and by providing a nitrogen-containing compound comprising ammonia;

soaking the titanium nitride layer in a silane ambient to form a titanium silicon nitride layer; and

depositing a copper seed layer over the titanium silicon nitride layer by self-ionizing plasma physical vapor deposition.